



**SB1620C THRU SB1660C**  
**SCHOTTKY BARRIER**  
**RECTIFIER**

**TECHNICAL**  
**SPECIFICATION**

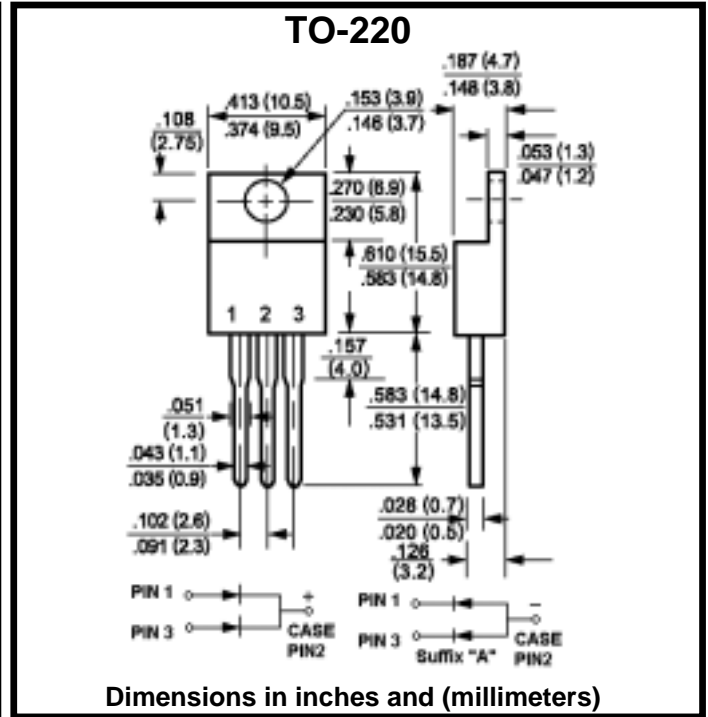
**VOLTAGE: 20 TO 60V CURRENT: 16A**

**FEATURES**

- Epitaxial construction for chip
- High current capability
- Low forward voltage drop
- Low power loss, high efficiency
- High surge capability
- High temperature soldering guaranteed:  
 250°C/10sec/0.375"(9.5mm) lead length  
 at 5 lbs tension

**MECHANICAL DATA**

- Terminal: Plated leads solderable per  
 MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O  
 recognized flame retardant epoxy
- Polarity: Common cathode, Suffix "A" Common anode
- Mounting position: Any



**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	SB 1620C	SB 1630C	SB 1635C	SB 1640C	SB 1650C	SB 1660C	UNITS
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	20	30	35	40	50	60	V
Maximum RMS Voltage	$V_{RMS}$	14	21	25	28	35	42	V
Maximum DC Blocking Voltage	$V_{DC}$	20	30	35	40	50	60	V
Maximum Average Forward Rectified Current ( $T_C=95^\circ C$ )	$I_{F(AV)}$	16						A
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	$I_{FSM}$	150						A
Maximum Forward Voltage (at 8.0A DC)	$V_F$	0.65				0.75		V
Maximum DC Reverse Current (at rated DC blocking voltage)	$I_R$	5.0 50.0						mA mA
Typical Junction Capacitance (Note 1)	$C_J$	700				500		pF
Typical Thermal Resistance (Note 2)	$R_\theta(ja)$	3						°C/W
Operating Junction Temperature	$T_J$	-65 to +125				-65 to +150		°C
Storage Temperature	$T_{STG}$	-65 to +150						°C

Note:

1. Measured at 1.0 MHz and applied reverse voltage of  $4.0V_{dc}$
2. Thermal resistance from junction to case
3. Suffix "A" common anode